

N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

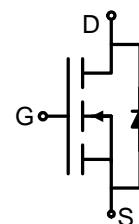
The PW3400 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

GENERAL FEATURES

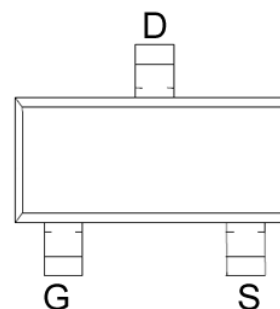
- $V_{DS} = 30V, I_D = 5.7A$
- $R_{DS(ON)} < 33m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 44m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 60m\Omega @ V_{GS}=2.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	5.7	A
Drain Current-Pulsed (Note 1)	I_{DM}	25	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V



Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6	0.85	1.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5.7A$	-	24	33	m Ω
		$V_{GS}=4.5V, I_D=3A$	-	28	44	m Ω
		$V_{GS}=2.5V, I_D=2A$	-	41	60	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	10	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	820	-	PF
Output Capacitance	C_{OSS}		-	99	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	77	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=2.7\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	3.3	-	nS
Turn-on Rise Time	t_r		-	4.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=5.8A,$ $V_{GS}=4.5V$	-	9.5	-	nC
Gate-Source Charge	Q_{gs}		-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=5.8A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	5.8	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

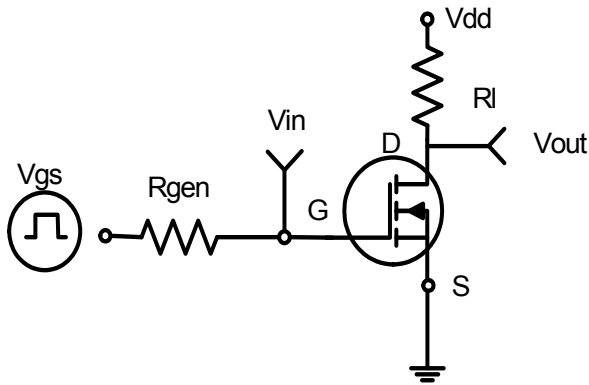


Figure 1: Switching Test Circuit

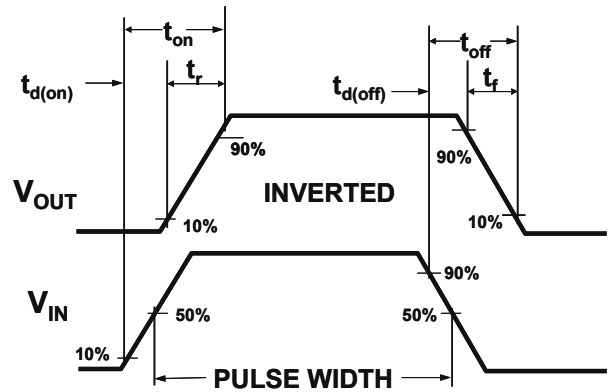


Figure 2: Switching Waveforms

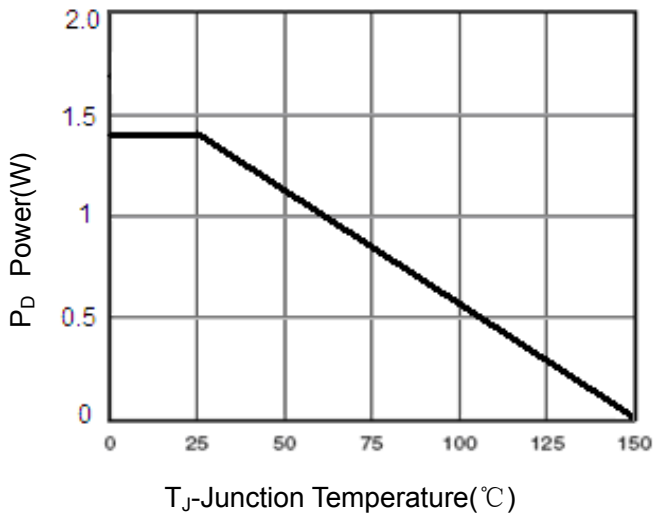


Figure 3 Power Dissipation

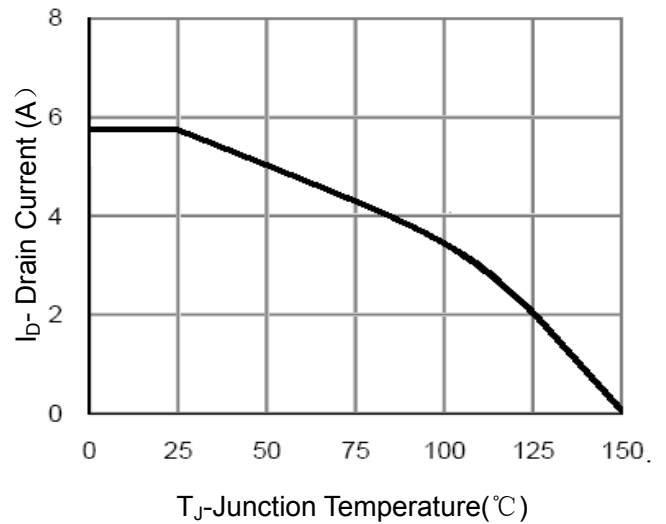


Figure 4 Drain Current

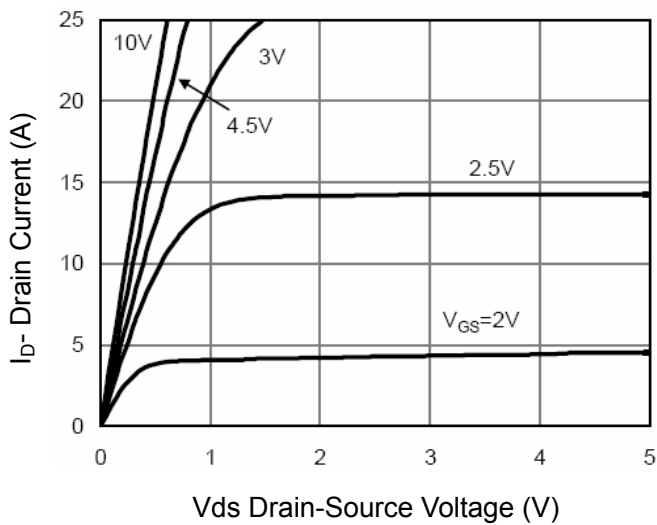


Figure 5 Output Characteristics

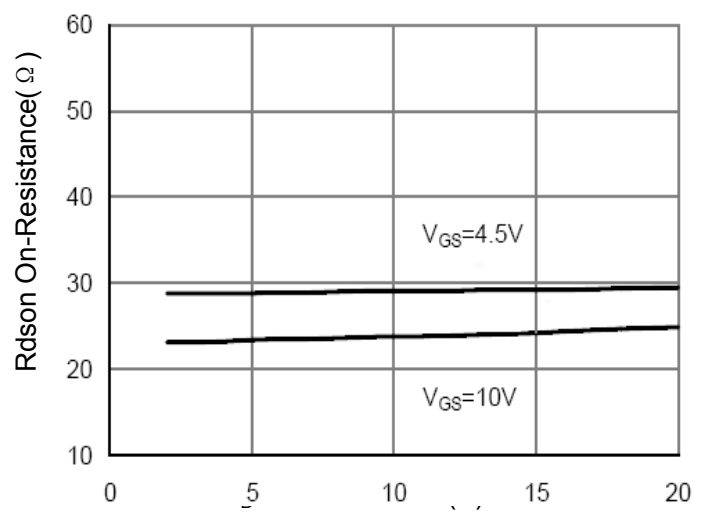


Figure 6 Drain-Source On-Resistance

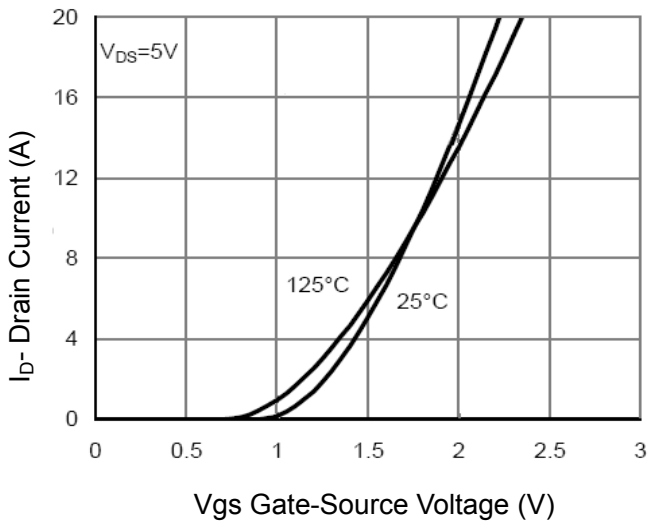


Figure 7 Transfer Characteristics

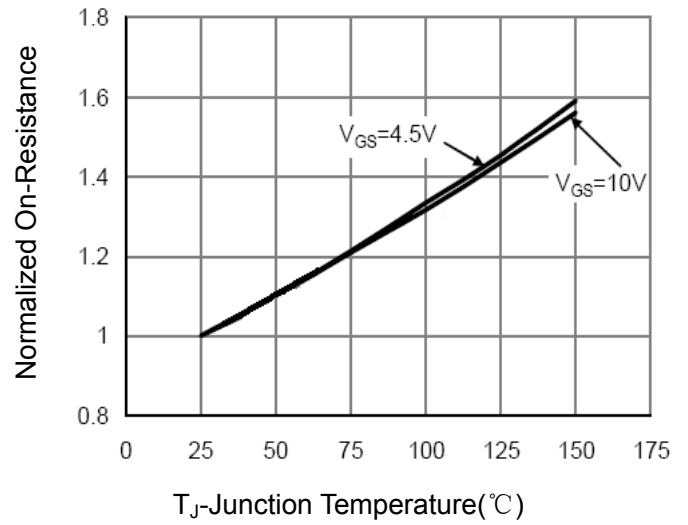


Figure 8 Drain-Source On-Resistance

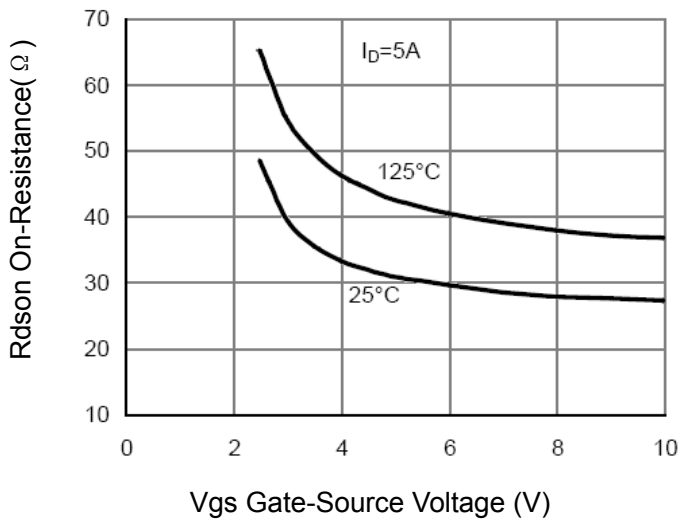


Figure 9 $R_{DS(on)}$ vs V_{GS}

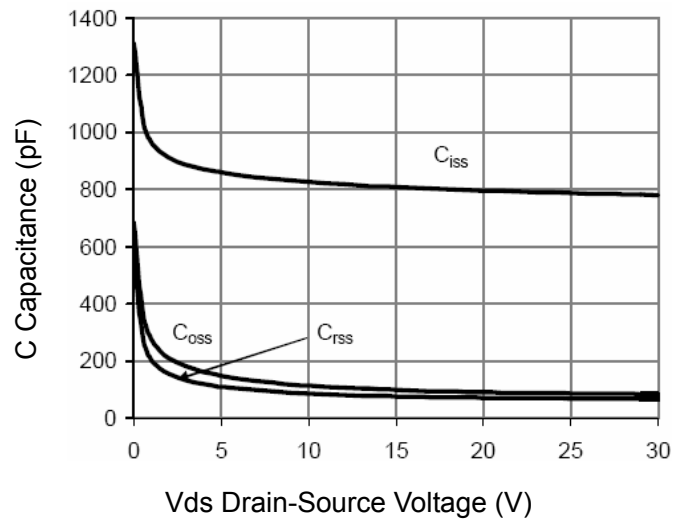


Figure 10 Capacitance vs V_{DS}

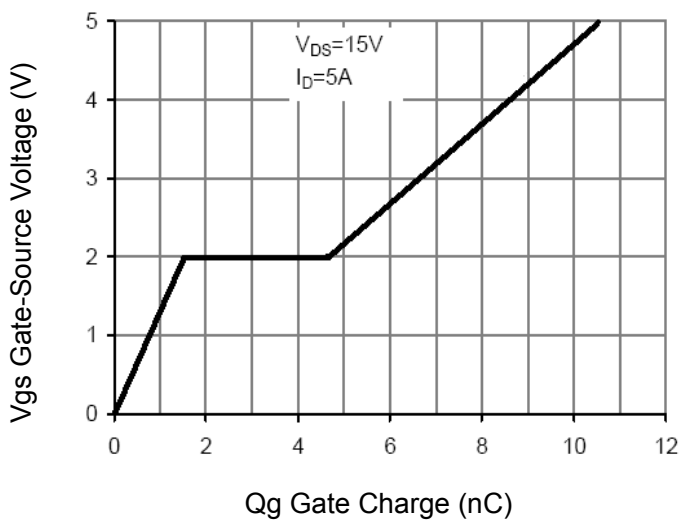


Figure 11 Gate Charge

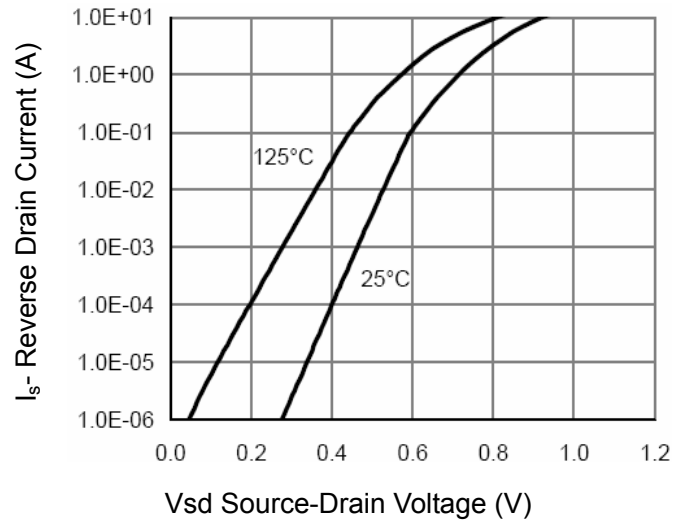


Figure 12 Source- Drain Diode Forward

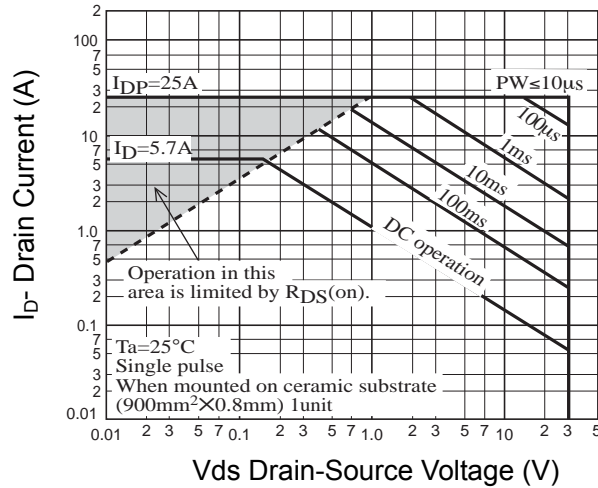


Figure 13 Safe Operation Area

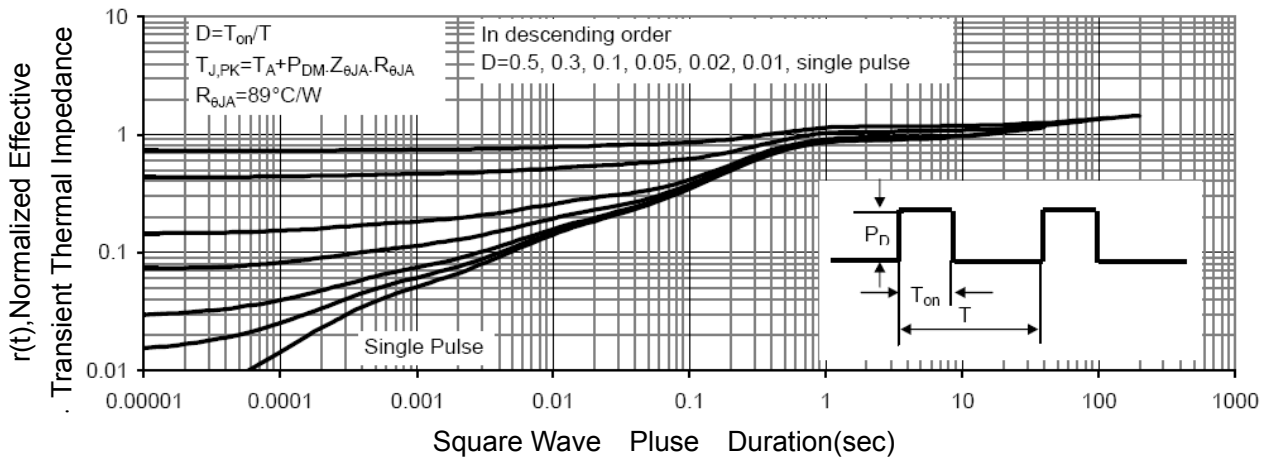
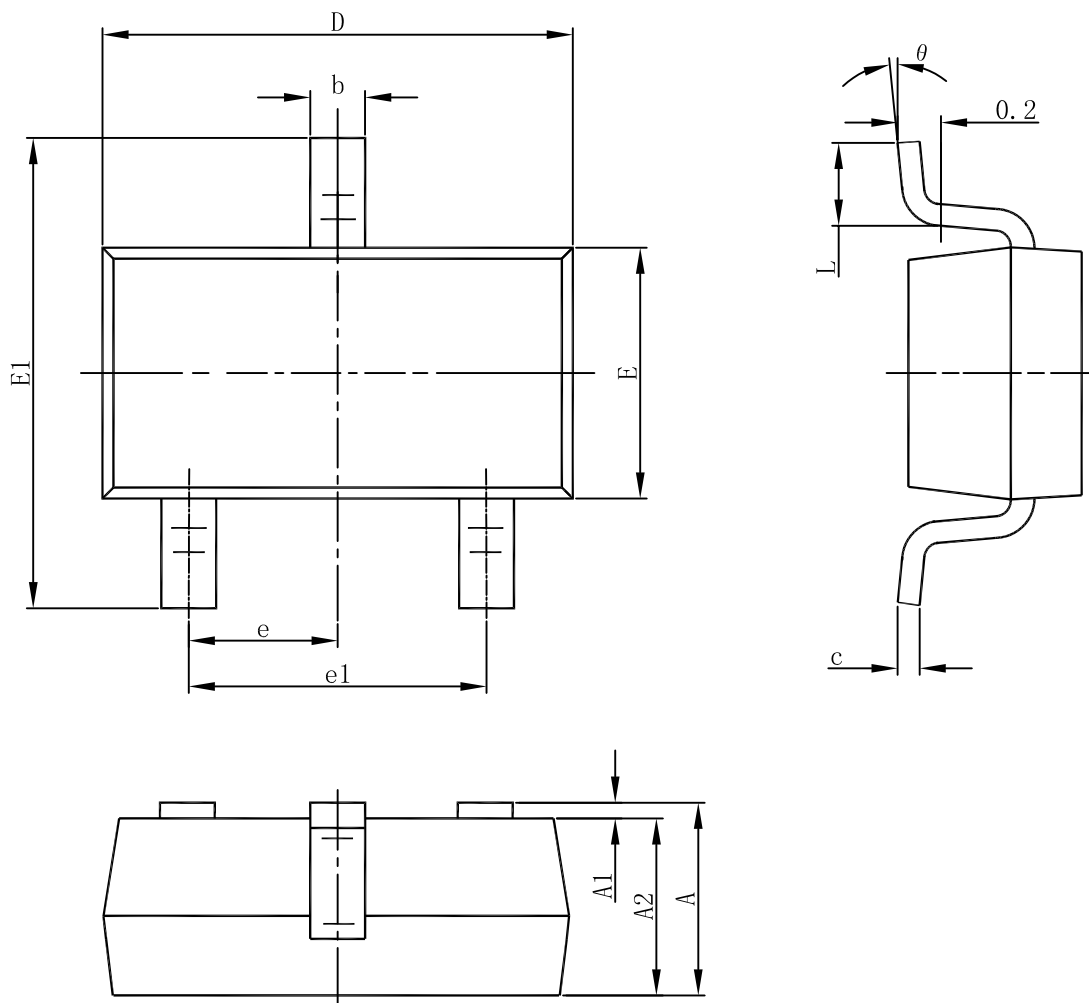


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23-3L PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°